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Inclosure Material:	
Metal	
Overall Length:	
1.253 inches	
Overall Diameter:	
0.505 inches	
Mounting Facility Qu	antity:
1	
Joint Electronic Devi	ce Engineering Council/jedec/case Outline Designation:
Do-4	
Electrode Internally-	electrically Connected To Case:
Anode	
Mounting Method:	
Threaded stud	
Overall Width Across	s Flats:
Between 0.423 inches	and 0.438 inches
Thread Size:	
0.190 inches	
Semiconductor Mate	rial:
Silicon	
Voltage Rating In Vo	Its Per Characteristic:
12.0 regulator voltage	3
Voltage Tolerance In	Percent:
5.0/+5.0	
Current Rating Per C	haracteristic:
210.00 milliamperes s	ource cutoff current horsepower metric
Power Rating Per Ch	aracteristic:
10.0 watts small-signa	I input power, common-collector preset
Maximum Operating	Tempurature Per Measurement Point:
175.0 degrees celsius	junction
Precious Material An	d Location:
Terminal surface optic	n silver or gold
Precious Material:	
Gold or silver	
Test Data Document	
81349-mil-s-19500 sp	ecification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes com	mercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and per	formance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Desig	nator:
Unf	
Terminal Type And C	uantity:
1 tab, solder lug and	threaded stud
Specification Data:	
81349-mil-s-19500/12	4 government specification

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Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0

